



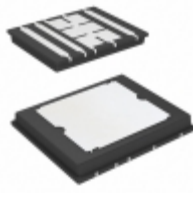


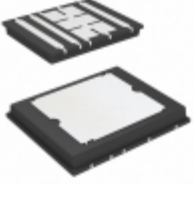
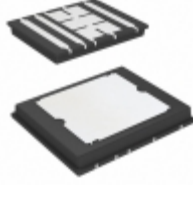
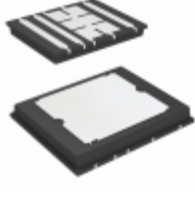
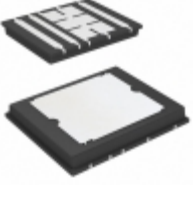
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|---|--|
|  | <h2 style="color: red;">SIE874DF-T1-GE3</h2> |
| | <p>Hersteller-Teilenummer: SIE874DF-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET N-CH 20V 60A POLARPAK</p> <p>Datenblätter:  SIE874DF-T1-GE3.pdf</p> <p>RoHS Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 3000 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p> |
| <p>Image may be representation. See specs for product details.</p> | |

Spezifikationen

| | |
|--|---|
| Teilenummer | SIE874DF-T1-GE3 |
| Hersteller | Electro-Films (EFI) / Vishay |
| Beschreibung | MOSFET N-CH 20V 60A POLARPAK |
| Kategorie | Diskrete Halbleiterprodukte > Transistoren-FETs, |
| Teilstatus | 3000 pcs Stock |
| detaillierte Beschreibung | N-Channel 20V 60A (Tc) 5.2W (Ta), 125W (Tc) Surface |
| Serie | TrenchFET® |
| Technologie | MOSFET (Metal Oxide) |
| Betriebstemperatur | -55°C ~ 150°C (TJ) |
| Befestigungsart | Surface Mount |
| Verpackung / Gehäuse | 10-PolarPAK® (L) |
| Supplier Device-Gehäuse | 10-PolarPAK® (L) |
| Verlustleistung (max) | 5.2W (Ta), 125W (Tc) |
| Typ FET | N-Channel |
| FET-Merkmal | - |
| Drain-Source-Spannung (Vdss) | 20V |
| Strom - Ununterbrochener Abfluss (Id) bei 25 ° C | 60A (Tc) |
| Rds On (Max) @ Id, Vgs | 1.17 mOhm @ 20A, 10V |
| VGS (th) (Max) @ Id | 2.2V @ 250µA |
| Gate Charge (Qg) (Max) @ Vgs | 145nC @ 10V |
| Eingabekapazität (Ciss) (Max) @ Vds | 6200pF @ 10V |
| Antriebsspannung (Max Rds On, Min Rds On) | 4.5V, 10V |
| Vgs (Max) | ±20V |
| Verpackung | Original-Reel® |
| Bleifreier Status / RoHS-Status | Lead free / RoHS Compliant |
| Feuchtigkeitsempfindlichkeitsniveau (MSL) | 1 (Unlimited) |
| Andere Namen | SIE874DF-T1-GE3DKR |

SIE874DF-T1-GE3 ist neu im Original, Suche SIE874DF-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SIE874DF-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SIE874DF-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

| | | | |
|---|---|--|---|
|  <p>SIE874DF-T1-GE3 Vishay / Siliconix MOSFET N-CH 20V 60A POLARPAK</p> |  <p>SIE878DF-T1-GE3 Vishay / Siliconix MOSFET N-CH 25V 45A POLARPAK</p> |  <p>SIE878DF-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 25V 45A POLARPAK</p> |  <p>SIE864DP-T1-GE3 VISHAY SIE864DP-T1-GE3 VISHAY</p> |
|  <p>SIE876DF-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 60V 60A POLARPAK</p> |  <p>SIE868DF-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 40V 60A POLARPAK</p> |  <p>SIE864DF-T1-GE3 Vishay / Siliconix MOSFET N-CH 30V 45A POLARPAK</p> |  <p>SIE876DF-T1-GE3 Vishay / Siliconix MOSFET N-CH 60V 60A POLARPAK</p> |

heiße Teile

Mehr

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|--------------------|-------------------|-------------------|-----------------------|-----------------------|
| ⚙ AAT3221JS-1.5-T1 | ➡ BD10KA5WFP-E2 | ➡ BJHCS-LTS-100A | D C1608X5R1V155M080AC | ➡ C1608X8R1H104M080AB |
| ⊣ CAT28C64BJ-20 | ⚙ CPH3341-TL-E | D DF100DA160 | ➡ DTA123YEB | ➡ IHLM2525CZERR47M01 |
| ⚙ LT1006S8#TR | ⊣ MAX793SCSE | ⚙ MC33166D2T | ➡ MDD55A08N | ➡ NCP6343BFCCT1G |
| D NJM2391DL1-33TE1 | ⚙ NT6818UG | ⊣ PT5127E23F-K | ⚙ SBR3U30P1-7-F | ➡ SIE01-03 |
| ➡ SIE01-06 | ➡ SIE20031 | ⚙ SIE20034 | ⊣ SIE501.8LT | ➡ SIE503.3LT |
| ➡ SIE503.3LTR | ➡ SIE800DF-T1-E3 | D SIE800DF-T1-E3 | ⚙ SIE802DF-T1-E3 | ⊣ SIE802DF-T1-E3 |
| ⚙ SIE808DF-T1-E3 | D SIE808DF-T1-E3 | ➡ SIE812DF | ➡ SIE848DF-T1-E3 | ➡ SIE848DF-T1-E3 |
| ⊣ SIE862DF-T1-GE3 | ⚙ SIE862DF-T1-GE3 | ➡ SIE864DP-T1-GE3 | ➡ SIE874DF-T1-GE3 | ➡ SK45GH063 |
| ⚙ SST310-T1-GE3 | ⊣ ST7L35F2MC00A | ⚙ STD18GK12B | D TC621XCOA | ➡ TK11237BMCL |
| ➡ TPA6205A1DRBR | ⚙ TT50F10KCM | ⊣ UCC27714DR | ⚙ V-16506-1C25 | ➡ ZMM5246B-7-F |

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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